



SANYO Semiconductors

DATA SHEET

LA6569 — Monolithic Linear IC

5-channel Driver for Compact Disk Applications

Overview

The LA6569 is a 5-channel driver for optical disc drives that includes a regulator on/off circuit.

Features

- Power amplifier 5-channel built-in. (Bridge-connection (BTL) : 4-channel, H bridge : 1-channel)
- I_O max 1A.
- Level shift circuit built-in (except H bridge).
- Mute circuit (output ON/OFF) built-in.
(Operable with BTL AMP with MUTE1 : CH1 and MUTE2 : CH2 to 4 and not operable for the H bridge of 3.3VREG.)
- 3.3V regulator built-in (external PNP transistor).
- With a function to set the loading output voltage.
- Overheat protection circuit (thermal shutdown) built-in.
- Regulator ON/OFF circuit built-in.

Specifications

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Maximum supply voltage	V_{CC} max		14	V
Maximum output current	I_O max	Each output for H bridge, channel 1 to 4	1	A
Maximum input voltage	V_{INB} max		13	V
Mute pin voltage	V_{MUTE}		13	V
Allowable operation	P_d max	Independent IC	0.8	W
		*Mounted on a standard board	2.0	W
Operating temperature	T_{opr}		-30 to +85	$^\circ\text{C}$
Storage temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

*1 A circuit board for mounting (76.1mm×114.3mm×1.6mm, glass epoxy resin)

Recommended Operating Conditions at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
supply voltage	V_{CC}	Same for V_{CC} -VREG	4.5 to 13	V

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LA6569

Electrical Characteristics at $T_a = 25^{\circ}\text{C}$, $V_{CC1} = V_{CC2} = 8\text{V}$, $V_{REF} = 1.65\text{V}$, unless especially specified.

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
All blocks						
No-load current drain ON	I _{CC} -ON	FWD = REV = 0, All outputs ON *1		30	50	mA
No-load current drain OFF	I _{CC} -OFF	FWD = REV = 0, All outputs OFF *1		10	20	mA
VREF input voltage range	VREF-IN		1		V _{CC} -1.5	V
Thermal shutdown temperature	TSD	*2	150	175	200	°C
BTL AMP block (CH1 to CH4)						
Output offset voltage	VOFF	Voltage difference between outputs for BTL AMP, each channel. *3	-60		60	mV
Input voltage range	V _{IN}	Input voltage range for input for OP-AMP.	0		V _{CC} -1.5	V
Output voltage	V _O	Each voltage between V _O + and V _O - when R _L = 8Ω. *4	5.7	6.5		V
Closed-circuit voltage gain	VG	Input and output gain. *3	5.4	6	6.6	deg
Slew rate	SR	AMP Independent. Multiply 2 between outputs. *2		0.5		V/μs
MUTE ON voltage	VMUTE-ON	Each MUTE *5	2			V
MUTE OFF voltage	VMUTE-OFF	Each MUTE *5			0.5	V
Input AMP block (CH1 to CH4)						
Input voltage range	V _{IN} -OP		0		V _{CC} -1.5	V
Output current (SINK)	SINK-OP		2			mA
Output current (SOURCE)	SOURCE-OP	*6	300	500		μA
Output offset voltage	VOFF-OP		-10		10	mV
Loading block (CH5, H bridge)						
Output voltage	V _O -LOAD	Forward, reverse, R _L = 8Ω *4	5.7	6.5		V
Break output saturation voltage	VCE-BREAK	Output voltage at braking *7			0.3	V
Input low level	V _{IN} -L				1	V
Input high level	V _{IN} -H		2			V
Output set voltage	VCONT	I _O = 200mA (Between outputs), VCONT = 3V	2.9	3.15	3.4	V
Power supply block (PNP transistor : 2SB632K-use)						
3.3V supply output	V _{OUT}	I _O = 200mA	3.15	3.3	3.45	V
REG-IN SINK current	REG-IN-SINK	Base current to external PNP *8		10		mA
Line regulation	ΔVOLN	6V≤V _{CC} ≤12V		20	150	mV
Load regulation	ΔVOLD	5mA≤I _O ≤200mA		50	200	mV
Regulator ON	REG-EN-ON	Regulator ON *9	2			V
Regulator OFF	REG-EN-OFF	Regulator OFF *9			0.5	V

*1. Current dissipation that is a sum of V_{CC1} and V_{CC2} at no load.

*2. Design guarantee value.

*3. Input AMP is a BUFFER AMP.

*4. Voltage difference between both ends of load (8Ω). Output saturated.

*5. Output ON with MUTE : [H] and OFF with MUTE : [L] (HI impedance).

*6. The source of input OP-AMP is a constant current. As the $11\text{k}\Omega$ resistance to the next stage is a load, pay due attention when setting the input OP-AMP gain.

*7. Short (GND) brake used. SINK side output ON.

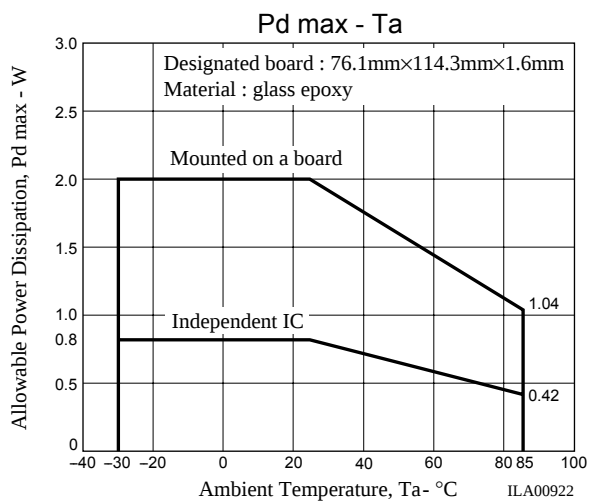
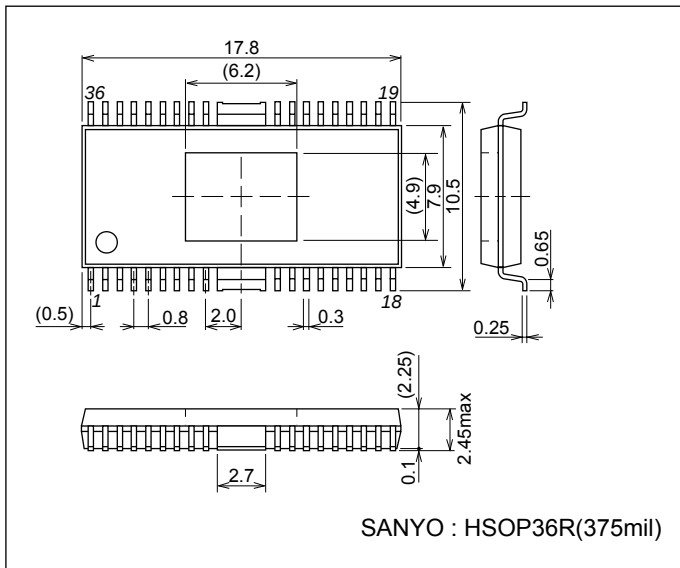
*8. 3.3VREG incorporates a drooping protection circuit and operated when the base current is 10mA (TYP).

*9. The output is 3.3V when the REG-EN pin is HIGH.

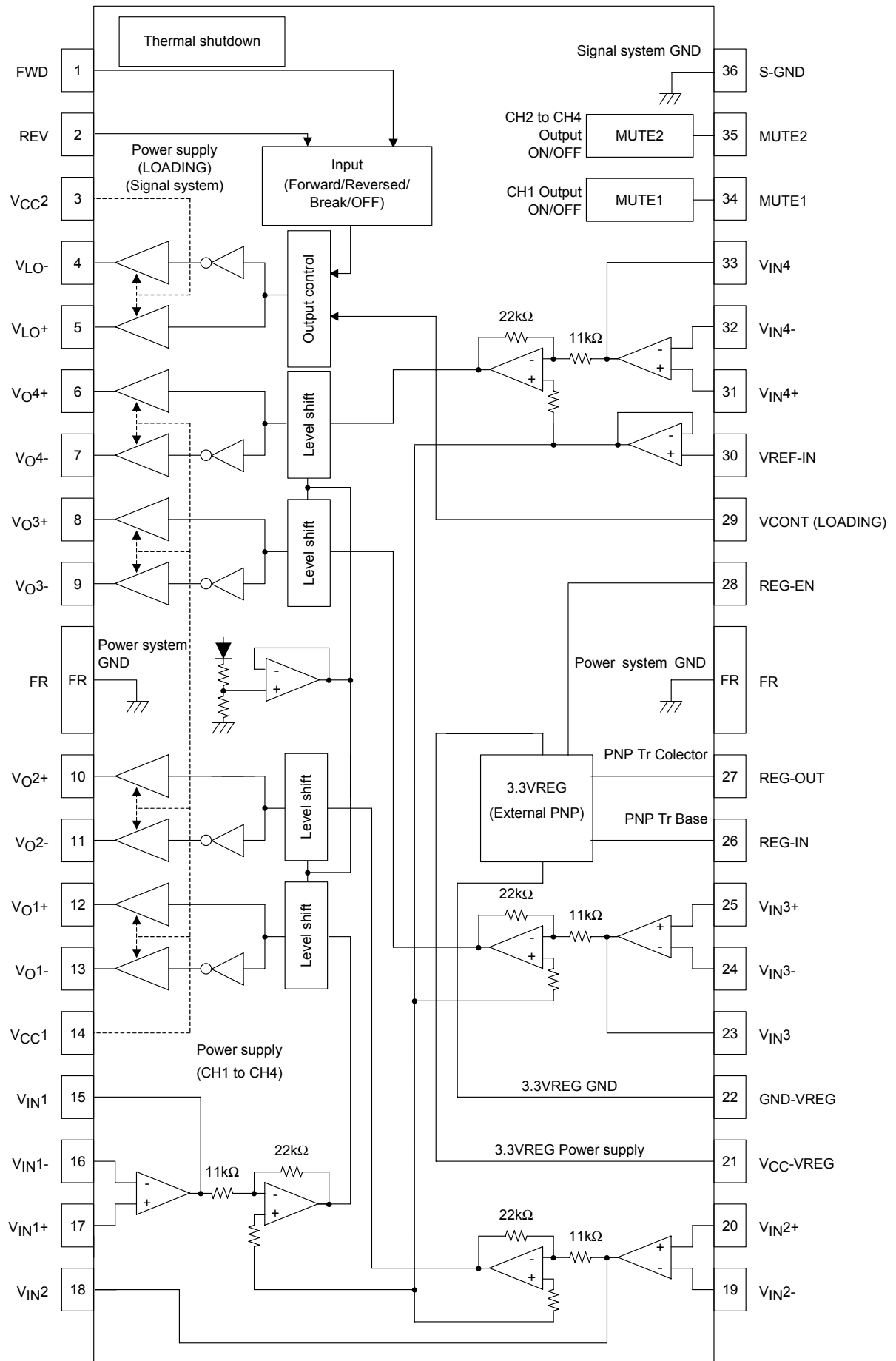
Package Dimensions

unit : mm

3251



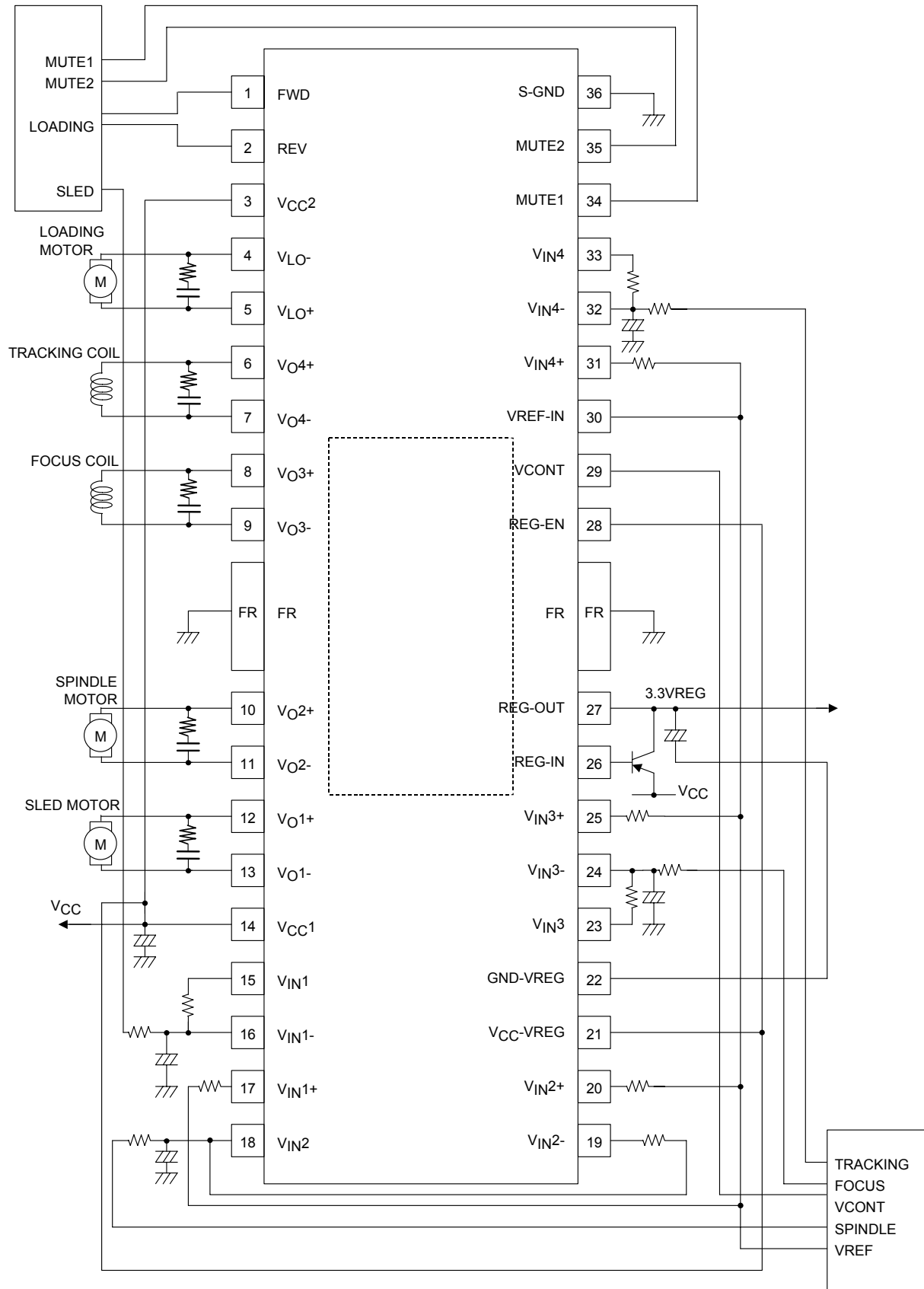
Block Diagram



Pin Description

Pin name	Pin name	Pin no.	Equivalent circuit	Pin explanation
Input (CH1 to 4)	V_{IN1+} V_{IN1-} V_{IN1} V_{IN2+} V_{IN2-} V_{IN2} V_{IN3+} V_{IN3-} V_{IN3} V_{IN4+} V_{IN4-} V_{IN4}	17 16 15 20 19 18 25 24 23 31 32 33		Input pin (CH1 to 4).
Input (LOADING)	FWD REV	1 2		Logic input pin. By combining H and L of this pin, any one of four modes (forward/reversed/brake/idling) can be selected.
Output (CH1 to 4)	V_{O1+} V_{O1-} V_{O2+} V_{O2-} V_{O3+} V_{O3-} V_{O4+} V_{O4-}	12 13 10 11 8 9 6 7		Output for channel 1 to 4.
MUTE	MUTE1 MUTE2	34 35		BTL AMP output. Output ON/OFF for CH1 to CH4. MUTE: H output ON MUTE: L output OFF
Output (LOADING)	V_{LO+} V_{LO-}	5 4		Output voltage set pin for loading block.

Sample Application Circuit



Note : Add CR between outputs or to a circuit to GND when oscillation occurs in the output.
Apply 4.5V or more to the external PNPT_r emitter pin.

Truth Table (loading (H bridge) section)

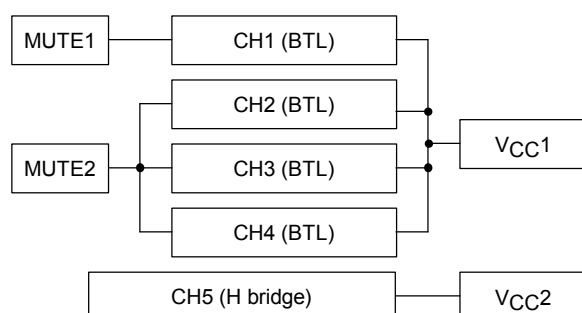
FWD	REV	Loading output
L	L	OFF *1
	H	Forward
H	L	Reversed
	H	(Short) brake *2

*1 The output has a high impedance.

*2 At brake, the SINK side transistor is ON (short brake).

V_{LO+} and V_{LO-} are approximately on the GND level.

Relation of MUTE and Power (V_{CC}^*)



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